

1200V / 10A

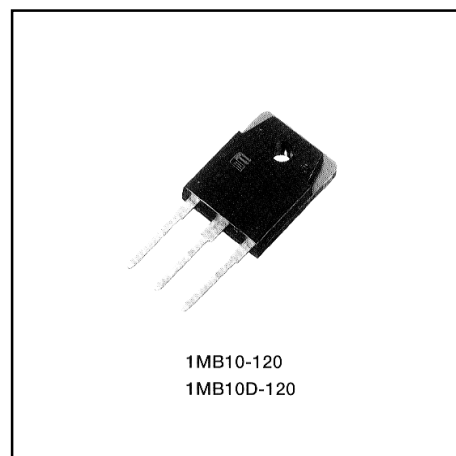
Molded Package

■ Features

- Small molded package
- Low power loss
- Soft switching with low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)
- Comprehensive line-up

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply



■ Maximum ratings and characteristics

- Absolute maximum ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

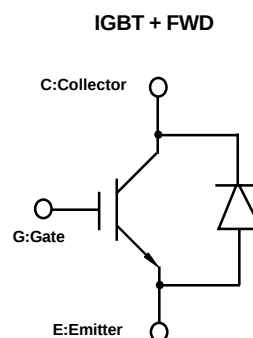
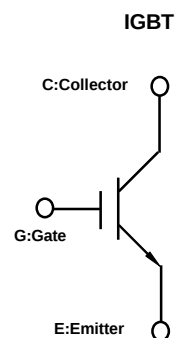
1MB10-120 / IGBT

Item			Symbol	Rating	Unit
Collector-Emitter voltage			V_{CES}	1200	V
Gate-Emitter voltage			V_{GES}	±20	V
Collector current	DC	Tc=25°C	Ic25	16	A
		Tc=100°C	Ic100	10	A
	1ms	Tc=25°C	Icp	48	A
Max. power dissipation(IGBT)			Pc	135	W
Operating temperature			Tj	+150	°C
Storage temperature			Tstg	-40 to +150	°C
Screw torque			-	50	N·m

1MB10D-120 / IGBT+FWD

Item			Symbol	Rating	Unit
Collector-Emitter voltage			V_{CES}	1200	V
Gate-Emitter voltage			V_{GES}	±20	V
Collector current	DC	Tc=25°C	Ic25	16	A
		Tc=100°C	Ic100	10	A
	1ms	Tc=25°C	Icp	48	A
Max. power dissipation (IGBT)			Pc	135	W
Max. power dissipation (FWD)			Pc	85	W
Operating temperature			Tj	+150	°C
Storage temperature			Tstg	-40 to +150	°C
Screw torque			-	50	N·m

■ Equivalent Circuit Schematic



● Electrical characteristics (at T_j=25°C unless otherwise specified)

1MB10-120 / IGBT

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Zero gate voltage collector current	I _{CEs}	—	—	1.0	V _{GE} =0V, V _{CE} =1200V	mA
Gate-Emitter leakage current	I _{GES}	—	—	20	V _{CE} =0V, V _{GE} =±20V	μA
Gate-Emitter threshold voltage	V _{GE(th)}	5.5	—	8.5	V _{CE} =20V, I _C =10mA	V
Collector-Emitter saturation voltage	V _{CE(sat)}	—	—	3.5	V _{GE} =15V, I _C =10A	V
Input capacitance	C _{ies}	—	1200	—	V _{GE} =0V	pF
Output capacitance	C _{oes}	—	250	—	V _{CE} =10V	
Reverse transfer capacitance	C _{res}	—	80	—	f=1MHz	
Turn-on time	t _{on}	—	—	1.2	V _{CC} =600V I _C =10A	μs
	t _r	—	—	0.6	V _{GE} =±15V	
Turn-off time	t _{off}	—	—	1.5	R _G =160 ohm	
	t _f	—	—	0.5	(Half Bridge)	

1MB10D-120 / IGBT+FWD

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Zero gate voltage collector current	I _{CEs}	—	—	1.0	V _{GE} =0V, V _{CE} =1200V	mA
Gate-Emitter leakage current	I _{GES}	—	—	20	V _{CE} =0V, V _{GE} =±20V	μA
Gate-Emitter threshold voltage	V _{GE(th)}	5.5	—	8.5	V _{CE} =20V, I _C =10mA	V
Collector-Emitter saturation voltage	V _{CE(sat)}	—	—	3.5	V _{GE} =15V, I _C =10A	V
Input capacitance	C _{ies}	—	1200	—	V _{GE} =0V	pF
Output capacitance	C _{oes}	—	250	—	V _{CE} =10V	
Reverse transfer capacitance	C _{res}	—	80	—	f=1MHz	
Turn-on time	t _{on}	—	—	1.2	V _{CC} =600V, I _C =10A	μs
	t _r	—	—	0.6	V _{GE} =±15V	
Turn-off time	t _{off}	—	—	1.5	R _G =160 ohm	
	t _f	—	—	0.5	(Half Bridge)	
FWD forward on voltage	V _F	—	—	3.0	I _F =10A, V _{GE} =0V	V
Reverse recovery time	t _{rr}	—	—	0.35	I _F =10A, V _{GE} =-10V, di/dt=100A/μs	μs

● Thermal resistance characteristics

1MB10-120 / IGBT

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Thermal resistance	R _{th(j-c)}	—	—	0.92	IGBT	°C/W

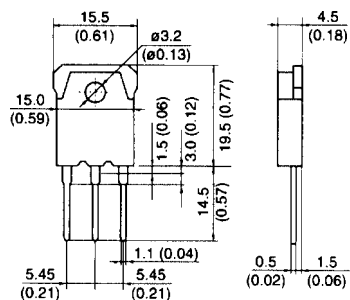
1MB10D-120 / IGBT+FWD

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Thermal resistance	R _{th(j-c)}	—	—	0.92	IGBT	°C/W
	R _{th(j-c)}	—	—	1.47	FWD	°C/W

■ Outline drawings, mm

1MB10-120, 1MB10D-120

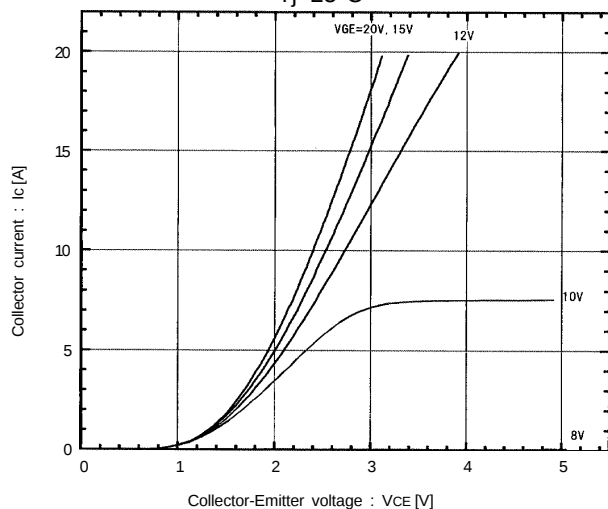
TO-3P



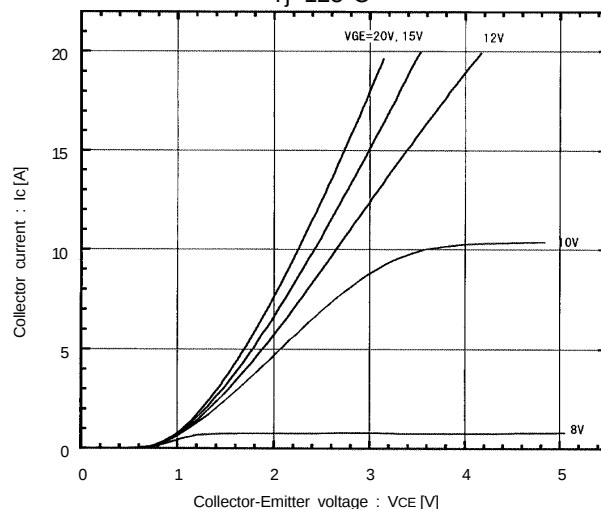
Characteristics

1MB10-120, 1MB10D-120

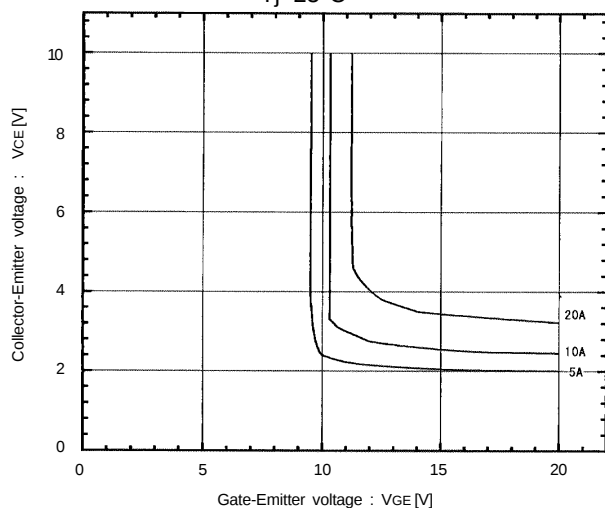
Collector current vs. Collector-Emitter voltage

 $T_j = 25^\circ\text{C}$ 

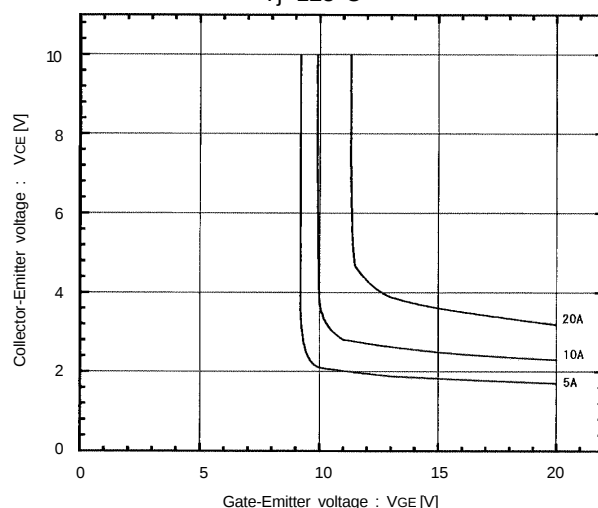
Collector current vs. Collector-Emitter voltage

 $T_j = 125^\circ\text{C}$ 

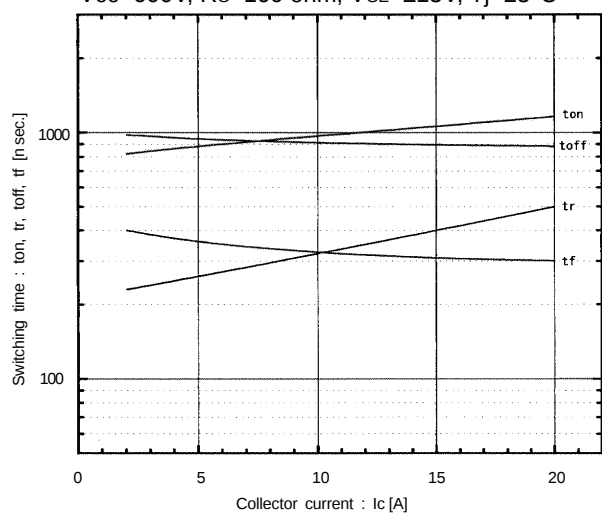
Collector-Emitter vs. Gate-Emitter voltage

 $T_j = 25^\circ\text{C}$ 

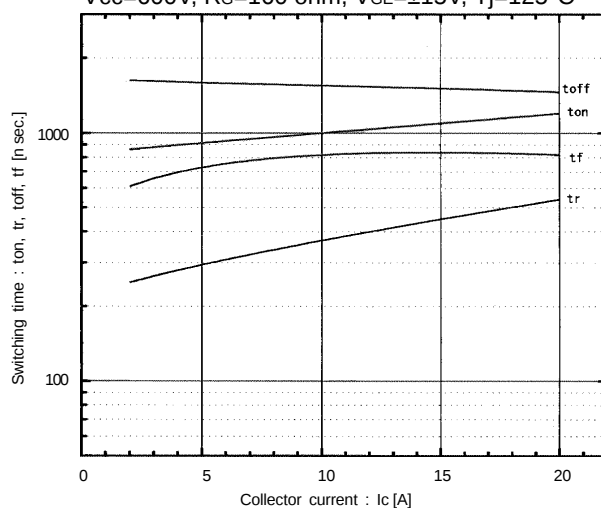
Collector-Emitter vs. Gate-Emitter voltage

 $T_j = 125^\circ\text{C}$ 

Switching time vs. Collector current

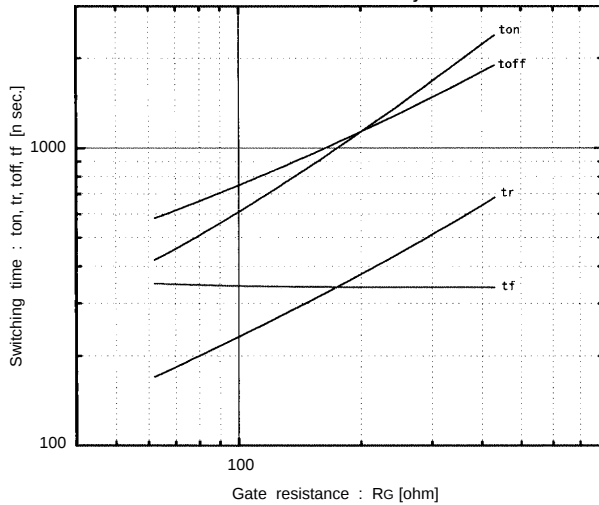
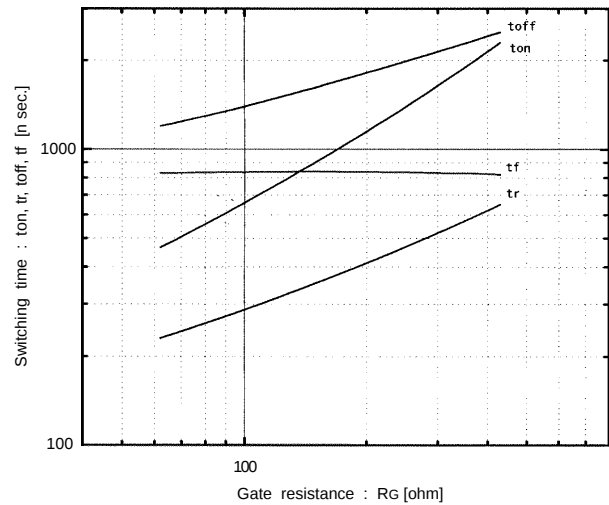
 $V_{CC} = 600\text{V}, R_G = 160\ \Omega, V_{GE} = \pm 15\text{V}, T_j = 25^\circ\text{C}$ 

Switching time vs. Collector current

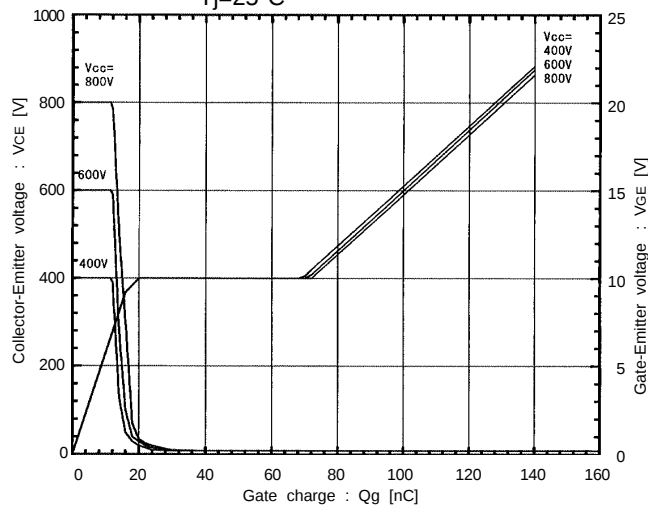
 $V_{CC} = 600\text{V}, R_G = 160\ \Omega, V_{GE} = \pm 15\text{V}, T_j = 125^\circ\text{C}$ 

Characteristics

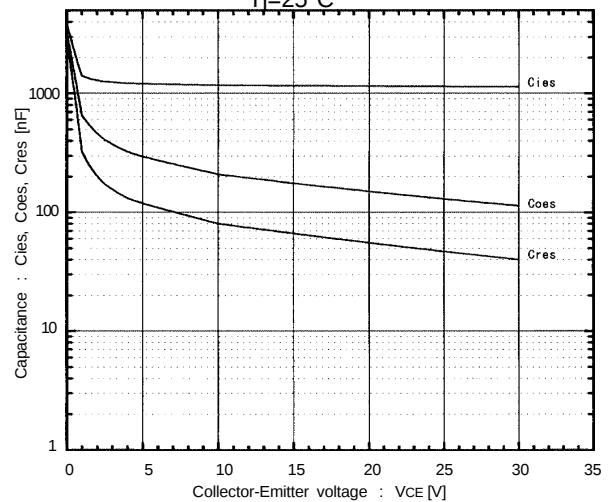
1MB10-120, 1MB10D-120

Switching time vs. R_G $V_{CC}=600V$, $I_C=10A$, $V_{GE}=\pm 15V$, $T_J=25^\circ C$ Switching time vs. R_G $V_{CC}=600V$, $I_C=10A$, $V_{GE}=\pm 15V$, $T_J=125^\circ C$ 

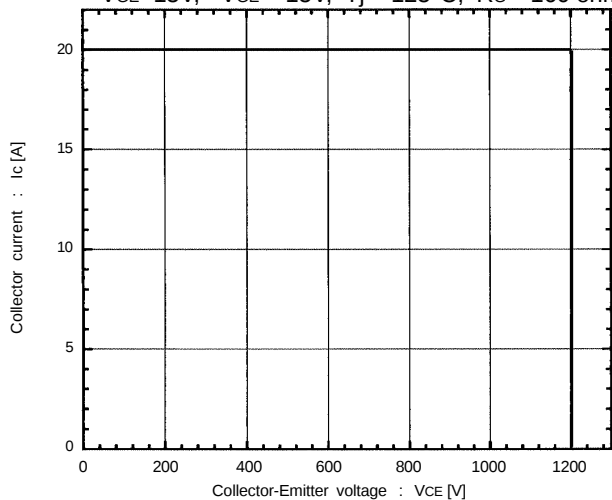
Dynamic input characteristics

 $T_J=25^\circ C$ 

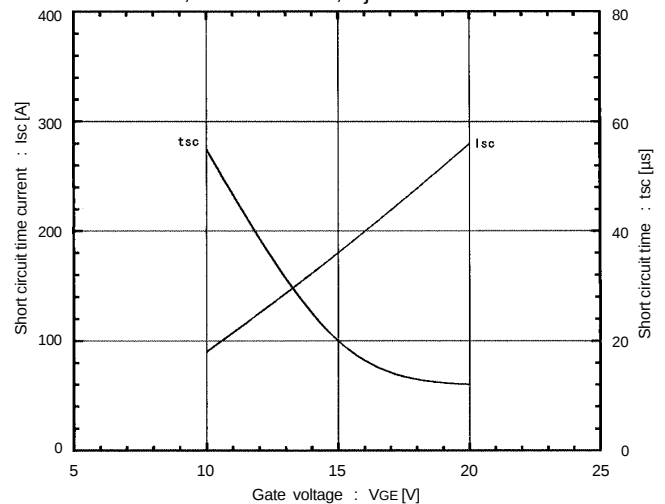
Capacitance vs. Collector-Emitter voltage

 $T_J=25^\circ C$ 

Reversed biased safe operating area

 $+V_{GE}=15V$, $-V_{GE} \leq 15V$, $T_J \leq 125^\circ C$, $R_G \geq 160 \text{ ohm}$ 

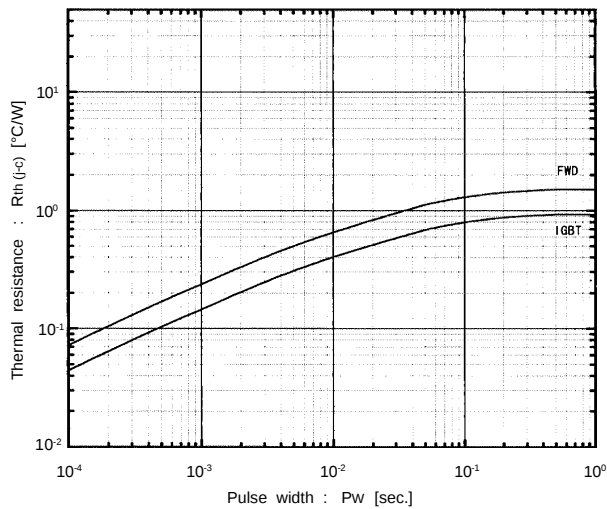
Typical short circuit capability

 $V_{CC}=800V$, $R_G=160 \text{ ohm}$, $T_J=125^\circ C$ 

Characteristics

1MB10-120, 1MB10D-120

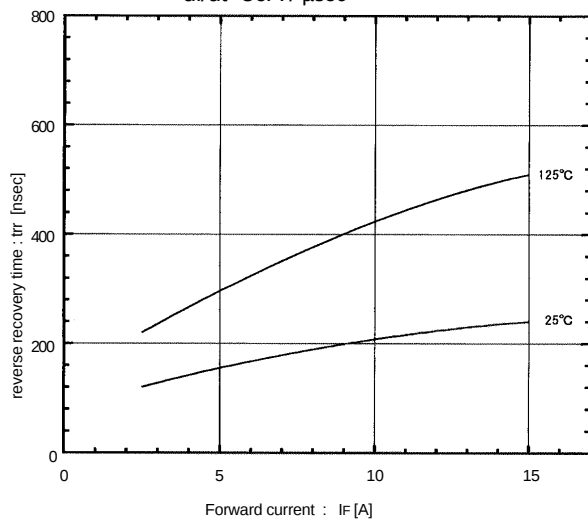
Transient thermal resistance



1MB10D-120

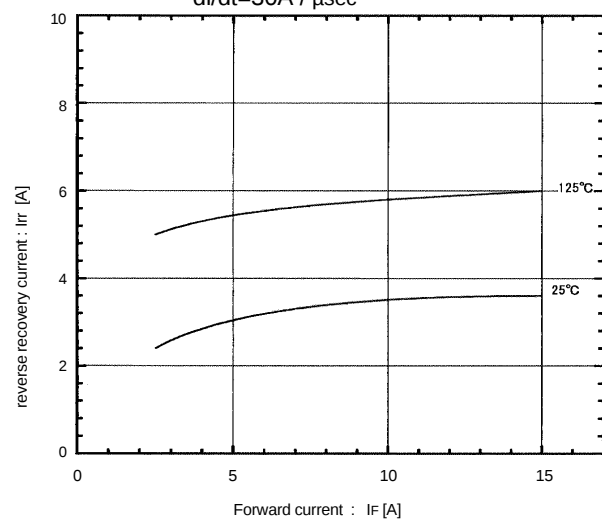
Reverse recovery time vs. Forward current

$-di/dt=30\text{A} / \mu\text{sec}$

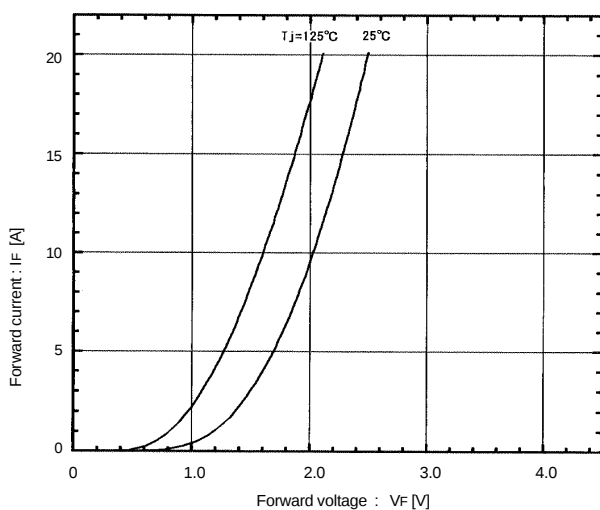


Reverse recovery current vs. Forward current

$-di/dt=30\text{A} / \mu\text{sec}$



Forward current vs. Forward voltage



Reverse recovery time characteristics vs. $-di/dt$

$I_F=10\text{A}, T_J=125^{\circ}\text{C}$

